

XP23 / XP26 Series

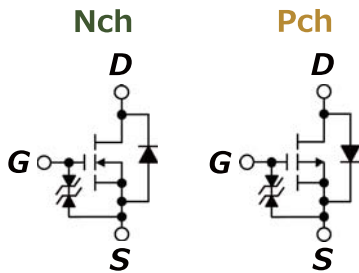
Nch / Pch MOSFETs in SOT-23 Package



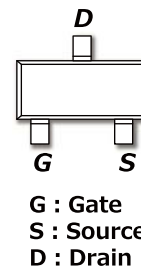
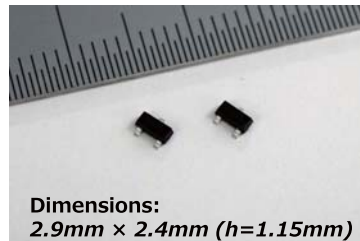
特長

- ・ゲート保護ダイオード内蔵
- ・低オン抵抗
- ・高速スイッチング

内部接続図



パッケージ情報



用途

- ・汎用
- ・スイッチング回路
- ・リレー回路

N-channel MOSFETs

Ta=25°C

Status	Part	Absolute Maximum Ratings			Electrical Characteristics				V _{GS(off)} (V)	
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	R _{DS(ON)} (Ω)				MIN.	MAX.
					V _{GS} =1.8(V) TYP.	V _{GS} =2.5(V) TYP.	V _{GS} =4.5(V) TYP.	V _{GS} =10(V) TYP.		
Under Development	XP231N0201TR-G	30	±20	0.15	-	5.5	3	-	0.8	1.8
New	XP232N0301TR-G	30	±20	0.3	-	-	1.7	1.1	0.9	2.5
New	XP233N0501TR-G	30	±20	0.5	-	1.5	0.6	-	0.9	1.7
New	XP234N0801TR-G	30	±20	0.8	-	-	0.3	0.2	0.9	2.6
New	XP235N2001TR-G	30	±20	2	-	-	0.11	0.08	1	2.4
New	XP261N7002TR-G	60	±20	0.15	-	-	3.5	3	0.9	2.1
New	XP262N7002TR-G	60	±20	0.3	-	-	1.5	1.1	1.1	2.1
New	XP263N1001TR-G	60	±20	1	-	-	0.23	0.18	1.1	2.4
New	XP264N0301TR-G	60	±20	0.3	-	-	1.5	1.1	1.1	2.1
New	XP236N2001TR-G	30	±8	2	-	0.1	0.08	-	0.4	1.1

P-channel MOSFETs

Ta=25°C

Status	Part	Absolute Maximum Ratings			Electrical Characteristics				V _{GS(off)} (V)	
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	R _{DS(ON)} (Ω)				MIN.	MAX.
					V _{GS} =-1.8(V) TYP.	V _{GS} =-2.5(V) TYP.	V _{GS} =-4.5(V) TYP.	V _{GS} =-10(V) TYP.		
Under Development	XP231P0201TR-G	-30	±8	-0.2	-	4	3.2	-	-0.5	-1.2
Under Development	XP232P0501TR-G	-30	±8	-0.45	-	1.45	0.95	-	-0.4	-1.1
Under Development	XP233P1501TR-G	-30	±20	-1.5	-	-	0.22	0.13	-0.9	-1.9

